

# Resonant Powder Diffraction Study of Gallium Distribution in the Type I Clathrates $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$ and $\text{Sr}_4\text{Eu}_4\text{Ga}_{16}\text{Ge}_{30}$

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## Introduction

In recent years, there has been an intense search for new thermoelectric materials [1, 2]. Slack has proposed that a good material for thermoelectric applications should combine the electronic properties of a crystal (high charge carrier mobility) with the thermal transport properties of a glass (poor heat transport) [3, 4]. These seemingly contradictory requirements can be found in some clathrates with “rattling” guest species inside their cavities [5-7].

The clathrates have structures similar to the type I and type II gas hydrates [8], but the host frameworks are made up of group 13 and 14 elements and alkali, alkaline, earth, or rare earth atoms as the guests [7]. Previous studies indicate that the type I clathrates  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$  and  $\text{Sr}_4\text{Eu}_4\text{Ga}_{16}\text{Ge}_{30}$  are good candidates for thermoelectric applications (see Fig. 1) [9-11].

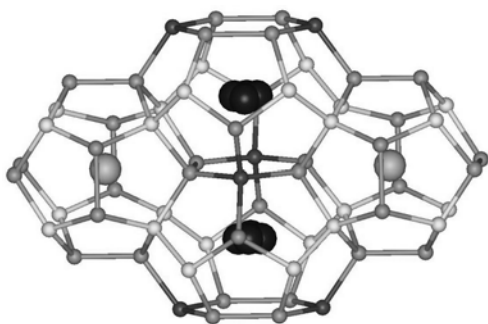


FIG. 1. The  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$  structure. In the framework, the black atoms occupy the  $6c$  sites, the light gray atoms occupy the  $16i$  sites, and the dark gray atoms occupy the  $24k$  sites. In the cavities, the gray atoms are at the  $\text{Sr}(1)$   $2a$  sites and the black atoms are at the  $\text{Sr}(2)$   $24k$  sites.

Little is known about the static disorder of gallium and germanium in their frameworks because of the lack of x-ray scattering contrast between gallium and germanium. Neutron diffraction provides only 10% contrast. Electronic structure calculations for  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$  suggest that the lowest energy arrangement of the framework components in this compound is nonrandom [12]. However, the neutron diffraction results suggest a random distribution of

gallium and germanium in  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$ . Compared with neutron and conventional x-ray diffraction, resonant x-ray scattering can provide considerably more contrast in the case of gallium and germanium.

## Methods and Materials

X-ray data were acquired at the SRI-CAT 1-BM beamline. Data sets recorded near the Ga and Ge K edges were employed for the examination of  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$ , and data sets recorded at the Ga, Ge, and Sr K edges were used to study  $\text{Sr}_4\text{Eu}_4\text{Ga}_{16}\text{Ge}_{30}$ . Transmission absorption spectra were obtained at the Ga, Ge, and Sr K edges from thin samples supported on tape. All diffraction patterns were collected at room temperature by using a flat-plate geometry with a Si(111) double-crystal sagittally focusing monochromator, a Si(111) analyzer crystal, and an Oxford Cyberstar detector. The program GSAS was employed for the Rietveld refinements (Fig. 2).

## Results and Discussion

The refinement for  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$  [ $a = 10.73637(4)$  Å, Pm-3n] shows a strong preference of gallium for the  $6c$  site [75.9(4)% occupancy] and a weaker preference for the  $24k$  site [43.2(3)% occupancy], with only 23.8(3)% occupancy of the  $16i$  site. These occupancy values are comparable to those previously suggested on the basis of electronic structure calculations. The stoichiometry from the refinement [ $\text{Sr}_8\text{Ga}_{18.74(9)}\text{Ge}_{27.26(9)}$ ] is only slightly different from what was expected ( $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$ ), which provides confidence in the results from the refinement.

The results from our analysis of  $\text{Sr}_4\text{Eu}_4\text{Ga}_{16}\text{Ge}_{30}$  [10.72768(1) Å] also strongly suggest a nonrandom distribution of gallium. The refined gallium occupancies for the  $6c$  [69.7(6)%],  $16i$  [18.0(5)%], and  $24k$  [30.9(4)%] sites are similar to those seen for  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$ , but there is a slight deficiency of Ga at the  $24k$  site in  $\text{Sr}_4\text{Eu}_4\text{Ga}_{16}\text{Ge}_{30}$  compared with  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$ . The refined stoichiometry ( $\text{Sr}_{4.53(3)}\text{Eu}_{3.47(3)}\text{Ga}_{14.48(13)}\text{Ge}_{31.52(13)}$ ) is in satisfactory agreement with what was expected ( $\text{Sr}_4\text{Eu}_4\text{Ga}_{16}\text{Ge}_{30}$ ).

Our observation that gallium atoms have a strong preference for the occupation of  $6c$  sites in both  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$  and  $\text{Sr}_4\text{Eu}_4\text{Ga}_{16}\text{Ge}_{30}$  is consistent with recent theoretical predictions and experimental observations of other type I clathrates that have no scattering contrast

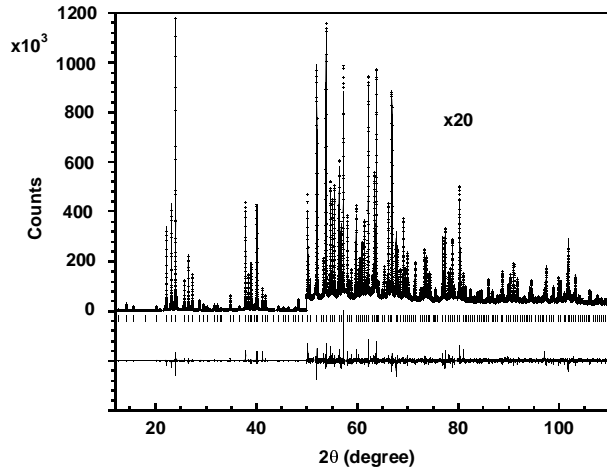


FIG. 2. The Rietveld fit to the 10.367-keV diffraction data for  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$ . Dots are the observed counts, continuous line is the best fit. The difference (obs - calc) is shown at the bottom of the plot, along with tag marks indicating the expected peak positions.

difficulties, but it is contrary to the reported neutron diffraction studies of  $\text{Sr}_8\text{Ga}_{16}\text{Ge}_{30}$  and  $\text{Eu}_8\text{Ga}_{16}\text{Ge}_{30}$  [11]. A more complete account of this work has recently been published [13].

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